



face has  $[\bar{1}10]$  Ga-As bonds and  $[110]$  In-As bonds. As a result, the two in-plane directions  $[110]$  and  $[\bar{1}10]$  are inequivalent,<sup>11-14</sup> and the symmetry is reduced to  $C_{2v}$  (four point group operations). Similarly, the  $\mathbf{k}\cdot\mathbf{p}$  does not recognize the proper odd-even symmetry of a film made of an odd or even number of monolayers,<sup>15</sup> or the correct  $C_{2v}$  symmetry of a self-assembled InAs/GaAs pyramidal dot.<sup>16</sup> The existence of a lower,  $C_{2v}$  symmetry in InAs/GaSb superlattices than the one ( $D_{2d}$ ) assumed in standard  $\mathbf{k}\cdot\mathbf{p}$  method has several consequences. (a)

(b) In our methodology the  $\mathbf{k}\cdot\mathbf{p}$  parameters are viewed as fixed constants not as adjustable parameters. Once determined from the bulk band structures (drawn from well-established experiments and state-of-the-art *ab initio* calculations, see below) they have not been readjusted to fit the superlattice experimental data, or the superlattice pseudopotential calculation. Indeed, in  $\mathbf{k}\cdot\mathbf{p}$  theory the input parameters are fundamentally bulk quantities, not properties of the nanostructures themselves.

## II. METHOD OF CALCULATION

We first determine screened pseudopotentials  $\{v_\alpha(q)\}$  as a function of momentum  $q$  for  $\alpha = \text{Ga, In, As, Sb}$ , using them to calculate the bulk band structures of GaSb and InAs from which we find the  $\mathbf{k}\cdot\mathbf{p}$  band parameters shown in Table I. These parameters are then used in an eight-band  $\mathbf{k}\cdot\mathbf{p}$  model<sup>4</sup> to calculate the superlattice states. Separately, the pseudopotentials  $\{v$

all-electron calculation the anion  $p$ -cation  $d$  coupling is fully

above (below) the InAs CBM (GaSb VBM) constitutes the electron (hole) confinement energy. We see that the pseudo-

that there is a finite amplitude there (unlike  $hh_2$  at  $n=20$ ). Such zone center lh-hh mixing and anticrossing are absent in the  $\mathbf{k}\cdot\mathbf{p}$  calculation. It is interesting to note, however, that this anticrossing does exist in  $\mathbf{k}\cdot\mathbf{p}$  at off  $\Gamma$  in-plane wave vectors. The quantitative difference in the lh energy levels (Table III) between pseudopotential and  $\mathbf{k}\cdot\mathbf{p}$  ranges from 145 meV at  $n=1$  to 9 meV at  $n=20$ .

#### IV. SUMMARY

The following points emerge from the comparison of pseudopotential and  $\mathbf{k}\cdot\mathbf{p}$  results.

- (1) The  $\mathbf{k}\cdot\mathbf{p}$  underestimates the electc39kabatesof61 T84J -1.2 -1.16652.8(en394-412.394-345.2(94-super(ca5.54(there)]TJ /F58 06f 1.6  
 $\mathbf{k}\cdot\mathbf{p}$

